	L #	Hits	Search Text	DBs	Time Stamp
1	L5	3564	(Si?sub.$3 near1 Ge?sub.$3) (SiGe GeSi)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 16:51
2	L12	138	strained adj2 (Si silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 17:08
3	L19	0	strained adj2 (Si/)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 17:08
4	L26	11	strained adj2 Si/SiGe	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 17:12
5	L33	71	5 and 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 17:12
6	L40	65	33 and (thick thickness nm nanometer ang angstrom micrometer ".mu.m")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 17:14
7	L47	1010	5 same (thick thickness nm nanometer ang angstrom micrometer ".mu.m")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 17:15
8	L54	54	12 and 47	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 19:00
9	L61	3	5906951.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 18:35
10	L68	77854	bond$3 near15 (temperature degree ".degree.C")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 19:17
11	L75	179	5 and 68	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 19:02
12	L82	6298	68 same (nitrogen or "N.sub.2" or air or argon or Ar)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 19:18
13	L89	15	5 and 82	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 19:04
14	L96	179693	bond$3 same (temperature degree ".degree.C")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 19:18
15	L103	20589	96 same (nitrogen or "N.sub.2" or air or argon or Ar)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 19:18
16	L110	48	5 and 103	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 19:19

	L #	Hits	Search Text	DBs	Time Stamp
1	L1	285	117/97.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 12:29
2	L8	3564	(Si?sub.$3 near1 Ge?sub.$3) (SiGe GeSi)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 12:29
3	L15	13210	silicon near1 germanium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 12:30
4	L22	14	1 and 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 13:07
5	L29	33	1 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 12:39
6	L36	23	29 not 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 12:39
7	L43	14438	((chemo chem chemical) near1 (mech mechanical)) near2 polish$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 13:09
8	L50	15461	cmp	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 13:42
9	L57	21517	43 50	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 13:43
10	L64	622	57 and (8 15)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 13:56
11	L71	129	64 and (bonded bonding)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 14:43
12	L78	95	64 and ((bonded bonding) near15 (wafer substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 13:58
13	L85	492	57 same (bonded bonding)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 14:14
14	L92	165	57 near20 (bonded bonding)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 14:14
15	L99	153	92 and (silicon or semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 14:15
16	L106	5	43 near20 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 14:42
17	L113	6861	43 near20 (si substrate wafer semiconductor silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 15:19
18	L120	62	113 same (RMS or roughness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 14:43
19	L127	17	120 and (bonded bonding)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 14:44
20	L134	92	(si substrate wafer semiconductor silicon) same rms same bond$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 15:20
21	L141	9	43 and 134	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 15:34
22	L148	0	2001WO-US19613.ap,prai.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 15:36
23	L155	0	2001WO-US19613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 15:36
24	L162	0	2001WO-US99169	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 15:36

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1	L1	3564	(Si?sub.$3 near1 Ge?sub.$3) (SiGe GeSi)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 11:10
2	L8	41	1 and (graded or gradient) and relaxed and bond$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 11:30
3	L15	6	1 and (stepped) and relaxed and bond$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 11:31